P-Channel 60-V (D-S) MOSFET

Key Features:

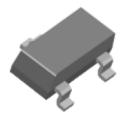
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

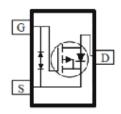
Typical	l Applications:
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- · White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)	
-60	700 @ V _{GS} = -10V	-1.2	
	800 @ V _{GS} = -4.5V	-1.1	









ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V_{DS}	-60	V	
Sate-Source Voltage		V_{GS}	±20	V	
Continuous Danis Comment [®]	T _A =25°C	1	-1.2		
Continuous Drain Current ^a	T _A =70°C	i _D	-0.9	Α	
Pulsed Drain Current ^b		I _{DM}	-5		
Continuous Source Current (Diode Conduction) ^a		I _S	-1.5	Α	
Downer Discipation 8	T _A =25°C	D	1.3	W	
Power Dissipation ^a	T _A =70°C	P _D	0.8		
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter			Maximum	Units	
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	100	°C/W	
Maximum Junction-to-Ambient	Steady State	МөлА	166		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

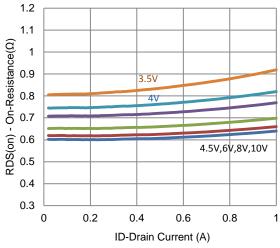
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	μA
Zero Gate Voltage Drain Current	1	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$			-1	 μA l
	I _{DSS}	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-2			Α
Drain-Source On-Resistance ^a	r	$V_{GS} = -10 \text{ V}, I_{D} = -1 \text{ A}$			700	mΩ
	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -0.8 \text{ A}$			800	
Forward Transconductance a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -1 \text{ A}$		8		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.8 \text{ A}, V_{GS} = 0 \text{ V}$		-0.88		V
		Dynamic ^b				
Total Gate Charge	Q_g	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$		1.1		nC
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -1 \text{ A}$		0.4		
Gate-Drain Charge	Q_gd	1D = 174		0.5		
Turn-On Delay Time	t _{d(on)}	V - 30 V B - 30 O		3		
Rise Time	t _r	$V_{DS} = -30 \text{ V}, R_{L} = 30 \Omega,$ $I_{D} = -1 \text{ A},$ $V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		5		ns
Turn-Off Delay Time	$t_{d(off)}$			8		
Fall Time	t _f			3		
Input Capacitance	C _{iss}			112		
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		11		pF
Reverse Transfer Capacitance	C_{rss}			8		

Notes

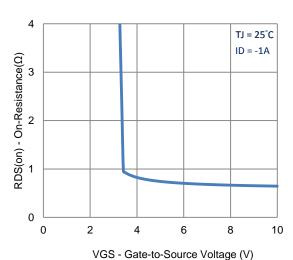
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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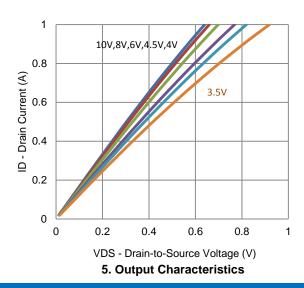
Typical Electrical Characteristics

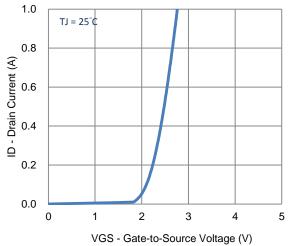


1. On-Resistance vs. Drain Current

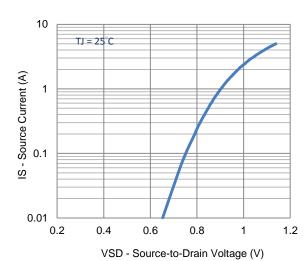


3. On-Resistance vs. Gate-to-Source Voltage

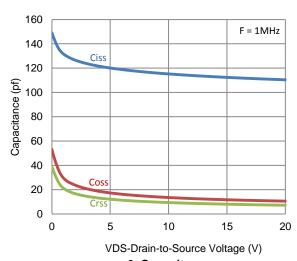




2. Transfer Characteristics



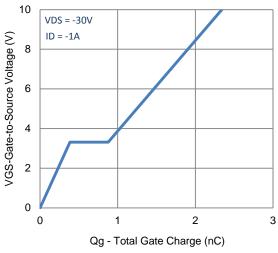
4. Drain-to-Source Forward Voltage



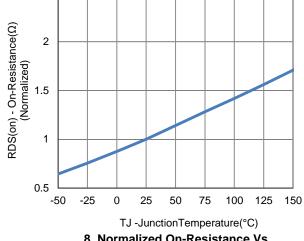
6. Capacitance

Typical Electrical Characteristics

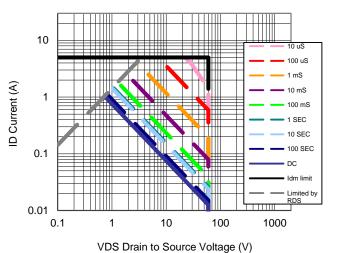
2.5



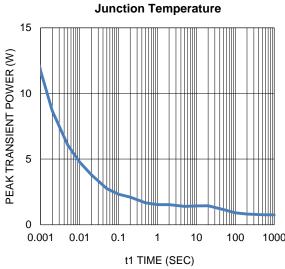




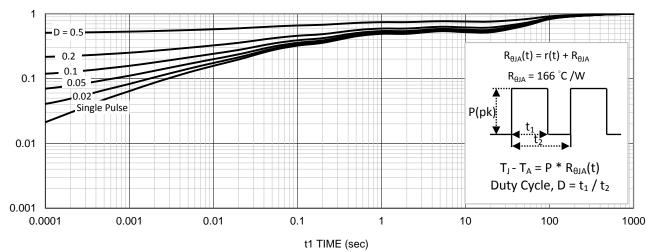
8. Normalized On-Resistance Vs



9. Safe Operating Area

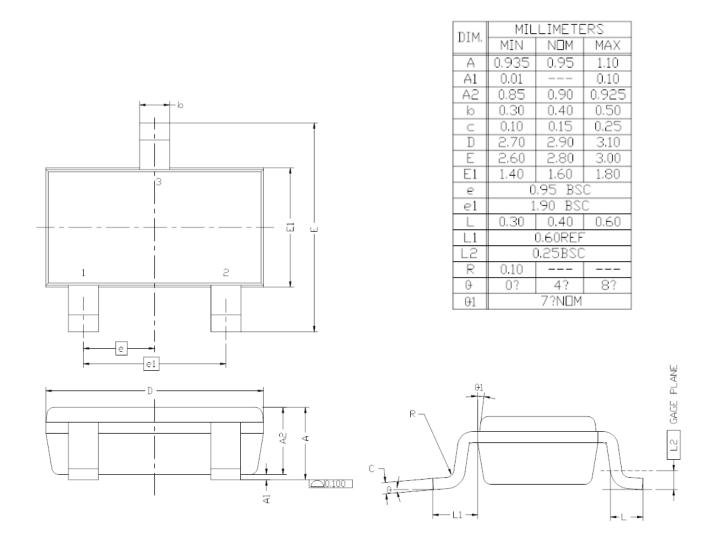


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- 5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.